











TLV369, TLV2369

SBOS757 - MAY 2016

# TLVx369 Cost-Optimized, 800-nA, 1.8-V, Rail-to-Rail I/O **Operational Amplifier with Zero-Crossover Distortion**

#### **Features**

Cost-Optimized Precision Amplifier *nano*Power: 800 nA/Ch (Typ)

Low Offset Voltage: 400 µV (Typ)

Rail-to-Rail Input and Output

**Zero-Crossover Distortion** 

Low Offset Drift: 0.5 μV/°C (Typ) Gain-Bandwidth Product: 12 kHz

Supply Voltage: 1.8 V to 5.5 V

microSize Packages: SC70-5, VSSOP-8

# **Applications**

**Blood Glucose Meters** 

**Test Equipment** 

Low-Power Sensor Signal Conditioning

Portable Devices

# 3 Description

The TLV369 family of single and dual operational amplifiers represents a cost-optimized generation of 1.8-V nanopower amplifiers.

With the zero-crossover distortion circuitry, these amplifiers feature high linearity over the full commonmode input range with no crossover distortion, enabling true rail-to-rail input and operating from a 1.8-V to 5.5-V single supply. The family is also compatible with industry-standard nominal voltages of 3.0 V, 3.3 V, and 5.0 V.

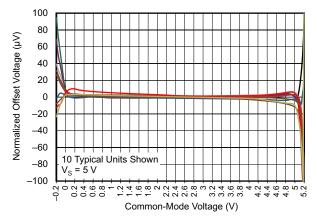
The TLV369 (single version) is offered in a 5-pin SC70 package. The TLV2369 (dual version) comes in 8-pin VSSOP and SOIC packages.

# Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TLV369	SC70 (5)	2.00 mm × 1.25 mm
TLV2369	VSSOP (8)	3.00 mm × 3.00 mm
1LV2369	SOIC (8)	4.90 mm × 3.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

# **TLV369 Family Eliminates Crossover Distortion** Across the Full Supply Range



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# 4 Revision History

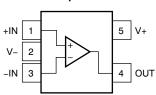
DATE	REVISION	NOTES
May 2016	*	Initial release.

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# 5 Pin Configuration and Functions

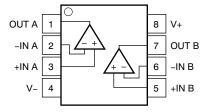
#### TLV369: DCK Package 5-Pin SC70 Top View



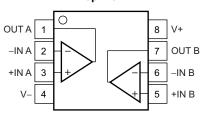
# Pin Functions: TLV369

PIN				
NAME	TLV369	I/O	DESCRIPTION	
NAME	DCK (SC70)			
-IN	3	I	Negative (inverting) input	
+IN	1	I	Positive (noninverting) input	
OUT	4	0	Output	
V-	2	_	Negative (lowest) power supply or ground (for single-supply operation)	
V+	5	_	Positive (highest) power supply	

# TLV2369: D Package 8-Pin SOIC Top View



## TLV2369: DGK Package 8-Pin VSSOP Top View



# Pin Functions: TLV2369

	PIN				
	TLV	2369	1/0	DESCRIPTION	
NAME	D (SOIC)	DGK (VSSOP)		DECOMM HON	
−IN A	2	2	I	Inverting input, channel A	
–IN B	6	6	I	Inverting input, channel B	
+IN A	3	3	I	Noninverting input, channel A	
+IN B	5	5	I	Noninverting input, channel B	
OUT A	1	1	0	Output, channel A	
OUT B	7	7	0	Output, channel B	
V-	4	4	_	Negative (lowest) power supply	
V+	8	8	_	Positive (highest) power supply	



# 6 Specifications

# 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	Supply, $V_S = (V+) - (V-)$	0	+7	V
	Signal input pin <sup>(2)</sup>	(V-) - 0.5	(V+) + 0.5	V
Current	Signal input pin <sup>(2)</sup>	-10	10	mA
	Output short-circuit <sup>(3)</sup>	Conti	Continuous	
	Operating, T <sub>A</sub>	-40	125	°C
Temperature	Junction, T <sub>J</sub>		150	°C
1	Storage, T <sub>stg</sub>	-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted).

			VALUE	UNIT
V	Flootroptotic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±4000	\/
V <sub>(ESD)</sub>	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted).

		MIN	NOM MAX	UNIT
Vs	Supply voltage	1.8	5.5	V
	Specified temperature	-40	85	°C

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**STRUMENTS** 

<sup>(2)</sup> Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.

<sup>(3)</sup> Short-circuit to  $V_{\mbox{\scriptsize S}}$  / 2, one amplifier per package.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



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6.4 Thermal Information: TI V369

o.4 The	mai imormation. TEV309		
		TLV369	
	THERMAL METRIC <sup>(1)</sup>	DCK (SC70)	UNIT
		5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	293.3	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	95.2	°C/W
R <sub>eJB</sub>	Junction-to-board thermal resistance	83.4	°C/W
₽ <sub>ЈТ</sub>	Junction-to-top characterization parameter	2.9	°C/W
Ψјв	Junction-to-board characterization parameter	82.4	°C/W
R <sub>B,IC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

# 6.5 Thermal Information: TLV2369

		TL\	TLV2369		
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	DGK (VSSOP)	UNIT	
		8 PINS	8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	121.5	168.5	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	66.3	58.1	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	62.5	88.9	°C/W	
ΨЈТ	Junction-to-top characterization parameter	22.8	9.3	°C/W	
ΨЈВ	Junction-to-board characterization parameter	61.9	87.6	°C/W	
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W	

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: TLV369 TLV2369

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# 6.6 Electrical Characteristics

 $V_S$  (total supply voltage) = 1.8 V to 5.5 V; at  $T_A$  = 25°C, and  $R_L$  = 100 k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)

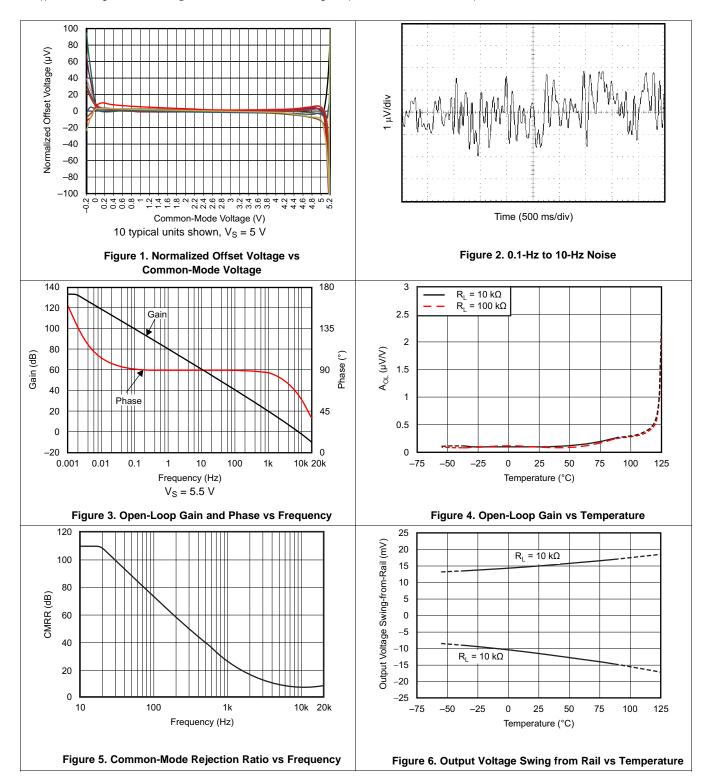
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE					
		At T <sub>A</sub> = 25°C		0.4	2	
Vos	Input offset voltage	At $T_A = -40$ °C to +85°C		0.85		mV
dV <sub>OS</sub> /dT	Drift	At $T_A = -40$ °C to +85°C		0.5		μV/°C
PSRR	Power-supply rejection ratio	V <sub>S</sub> = 1.8 V to 5.5 V	80	94		dB
INPUT VO	OLTAGE RANGE					
V <sub>CM</sub>	Common-mode voltage range		V-		V+	V
CMRR	Common-mode rejection ratio	$(V-) \le V_{CM} \le (V+)$	80	110		dB
INPUT BI	AS CURRENT	( ) OM ( )				
		At T <sub>A</sub> = 25°C		10		pA
I <sub>B</sub>	Input bias current	At T <sub>A</sub> = -40°C to +85°C	See Figure 8			<u> </u>
I <sub>os</sub>	Input offset current	Α		10		pA
	IPEDANCE					<u> </u>
Z <sub>ID</sub>	Differential			10 <sup>13</sup>    3		Ω    pF
Z <sub>IC</sub>	Common-mode			10 <sup>13</sup>    6		Ω    pF
NOISE	Common mode			10    0		12    Pi
E <sub>n</sub>	Input voltage noise	f = 0.1 Hz to 10 Hz		4		μV <sub>PP</sub>
	Input voltage noise density	f = 1 kHz		300		ηV <sub>PP</sub> nV/√ <del>Hz</del>
e <sub>n</sub>	Input voltage noise density	f = 1 kHz		1		fA/√Hz
OPENIC	DOP GAIN	I = I KIIZ				IAV VI IZ
OPEN-LU	JOP GAIN	At $V_S = 5.5 \text{ V}$ , 100 mV $\leq V_O \leq (V+) - 100 \text{ mV}$ ,				
A <sub>OL</sub>	Open-loop voltage gain	$R_L = 100 \text{ k}\Omega$		130		dB
/ OL	Open loop voltage gain	At $V_S = 5.5$ V, 500 mV $\leq$ $V_O \leq$ (V+) $-$ 500 mV, $R_L = 10$ k $\Omega$	80	120		ub_
OUTPUT						
Vo	Voltage output swing from rail	$R_L = 10 \text{ k}\Omega$			25	mV
I <sub>SC</sub>	Short-circuit current			10		mA
$C_{LOAD}$	Capacitive load drive		See	Figure 10		
FREQUE	NCY RESPONSE					
GBP	Gain bandwidth product			12		kHz
SR	Slew rate	G = 1		0.005		V/µs
t <sub>OR</sub>	Overload recovery time	$V_{IN} \times gain = V_{S}$		250		μs
POWER S	SUPPLY					
Vs	Specified voltage range		1.8		5.5	V
IQ	Quiescent current	$I_O = 0$ mA, at $V_S = 5.5$ V		800	1300	nA
TEMPER	ATURE					
	Specified range		-40		85	°C
T <sub>A</sub>	Operating range		-40		125	°C

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# 6.7 Typical Characteristics

at  $T_A$  = 25°C,  $V_S$  = 5 V, and  $R_L$  = 100 k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)

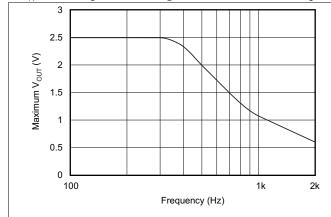


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# **Typical Characteristics (continued)**

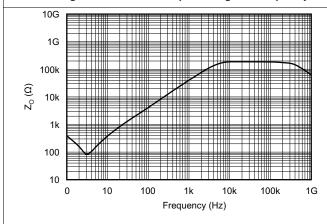
at  $T_A$  = 25°C,  $V_S$  = 5 V, and  $R_L$  = 100 k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)



10k 1k 100 100 100 100 0.01 -50 -25 0 25 50 75 100 125 Temperature (°C)

Figure 7. Maximum Output Voltage vs Frequency

Figure 8. Input Bias Current vs Temperature



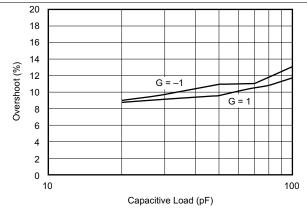
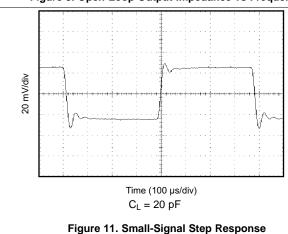


Figure 9. Open-Loop Output Impedance vs Frequency

Figure 10. Small-Signal Overshoot vs Capacitive Load



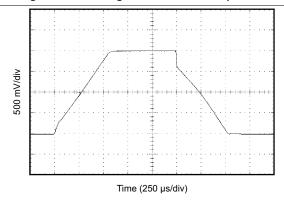


Figure 12. Large-Signal Step Response

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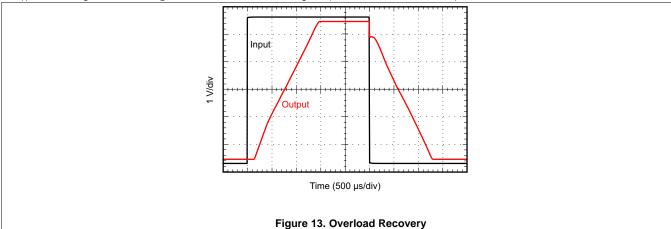
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# **Typical Characteristics (continued)**

at  $T_A$  = 25°C,  $V_S$  = 5 V, and  $R_L$  = 100 k $\Omega$  connected to  $V_S$  / 2 (unless otherwise noted)



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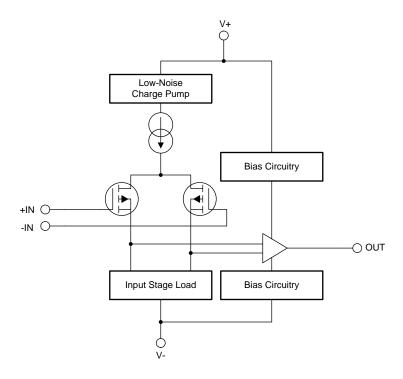


# 7 Detailed Description

# 7.1 Overview

The TLVx369 family of operational amplifiers minimizes power consumption and operates on supply voltages as low as 1.8 V. The zero-crossover distortion circuitry enables high linearity over the full input common-mode range, achieving true rail-to-rail input from a 1.8-V to 5.5-V single supply.

# 7.2 Functional Block Diagram



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# 7.3 Feature Description

# 7.3.1 Operating Voltage

The TLV369 series os op amps are fully specified and tested from 1.8 V to 5.5 V (±0.9 V to ±2.75 V). Parameters that vary significantly with supply voltage are described in the *Typical Characteristics* section.

## 7.3.2 Input Common-Mode Voltage Range

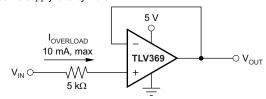
The TLV369 family is designed to eliminate the input offset transition region typically present in most rail-to-rail, complementary-stage operational amplifiers, allowing the TLV369 family of amplifiers to provide superior common-mode performance over the entire input range.

The input common-mode voltage range of the TLV369 family typically extends to each supply rail. CMRR is specified from the negative rail to the positive rail; see Figure 1, Normalized Offset Voltage vs Common-Mode Voltage.

# 7.3.3 Protecting Inputs from Overvoltage

Input currents are typically 10 pA. However, large inputs (greater than 500 mV beyond the supply rails) can cause excessive current to flow in or out of the input pins. Therefore, in addition to keeping the input voltage between the supply rails, the input current must also be limited to less than 10 mA. This limiting is easily accomplished with an input resistor, as shown in Figure 14.

> A current-limiting resistor is required if the input voltage exceeds the supply rails by  $\geq 0.5$  V.



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Figure 14. Input Current Protection for Voltages That Exceed the Supply Voltage

## 7.4 Device Functional Modes

The TLV369 family has a single functional mode. These devices are powered on as long as the power-supply voltage is between 1.8 V (±0.9 V) and 5.5 V (±2.75 V).

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# 8 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

# 8.1 Application Information

When designing for ultra-low power, choose system components carefully. To minimize current consumption, select large-value resistors. Any resistors can react with stray capacitance in the circuit and the input capacitance of the operational amplifier. These parasitic RC combinations can affect the stability of the overall system. Use of a feedback capacitor assures stability and limits overshoot or gain peaking.

# 8.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in Figure 15. An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier also makes negative input voltages positive on the output. In addition, amplification can be added by selecting the input resistor R<sub>I</sub> and the feedback resistor R<sub>F</sub>.

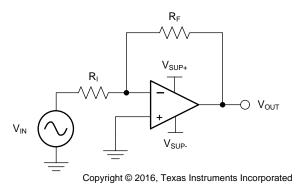


Figure 15. Application Schematic

## 8.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range ( $V_{CM}$ ) and the output voltage swing to the rails ( $V_O$ ) must also be considered. For instance, this application scales a signal of  $\pm 0.5$  V (1 V) to  $\pm 1.8$  V (3.6 V). Setting the supply at  $\pm 2.5$  V is sufficient to accommodate this application.

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# **Typical Application (continued)**

# 8.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using Equation 1 and Equation 2:

$$A_{V} = \frac{V_{OUT}}{V_{IN}} \tag{1}$$

$$A_{V} = \frac{1.8}{-0.5} = -3.6 \tag{2}$$

When the desired gain is determined, choose a value for R<sub>I</sub> or R<sub>F</sub>. Choosing a value in the kilohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures that the device does not draw too much current. The trade-off is that very large resistors (100s of kilohms) draw the smallest current but generate the highest noise. Very small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k $\Omega$  for R<sub>I</sub>, meaning 36 k $\Omega$  is used for R<sub>F</sub>. These values are determined by Equation 3:

$$A_{V} = -\frac{R_{F}}{R_{I}} \tag{3}$$

# 8.2.3 Application Curve

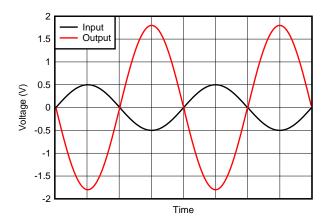


Figure 16. Inverting Amplifier Input and Output

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# 8.3 System Examples

# 8.3.1 Battery Monitoring

The low operating voltage and quiescent current of the TLV369 series make the family an excellent choice for battery-monitoring applications, as shown in Figure 17.

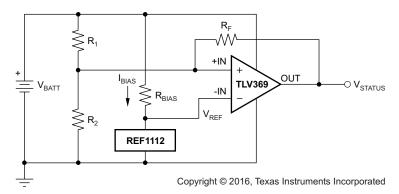


Figure 17. Battery Monitor

In this circuit,  $V_{STATUS}$  is high as long as the battery voltage remains above 2 V. A low-power reference is used to set the trip point. Resistor values are selected as follows:

1. Selecting R<sub>F</sub>: Select R<sub>F</sub> such that the current through R<sub>F</sub> is approximately 1000 times larger than the maximum bias current over temperature, as given by Equation 4:

$$R_{F} = \frac{V_{REF}}{1000 (I_{BMAX})}$$

$$= \frac{1.2 \text{ V}}{1000 (50 \text{ pA})}$$

$$= 24 \text{ M}\Omega \approx 20 \text{ M}\Omega$$
(4)

- 2. Choose the hysteresis voltage, V<sub>HYST</sub>. For battery-monitoring applications, 50 mV is adequate.
- 3. Calculate R<sub>1</sub> as calculated by Equation 5:

$$R_1 = R_F \left( \frac{V_{HYST}}{V_{BATT}} \right) = 20 \text{ M}\Omega \left( \frac{50 \text{ mV}}{2.4 \text{ V}} \right) = 420 \text{ k}\Omega$$
 (5)

- 4. Select a threshold voltage for  $V_{IN}$  rising  $(V_{THRS}) = 2.0 \text{ V}$ .
- 5. Calculate R<sub>2</sub> as given by Equation 6:

$$R_{2} = \frac{1}{\left[\left(\frac{V_{THRS}}{V_{BATT}}\right) - \frac{1}{R_{1}} - \frac{1}{R_{1}}\right]}$$

$$= \frac{1}{\left[\left(\frac{2 \text{ V}}{1.2 \text{ V} \times 420 \text{ k}\Omega}\right) - \frac{1}{420 \text{ k}\Omega} - \frac{1}{20 \text{ M}\Omega}\right]}$$

$$= 650 \text{ k}\Omega$$
(6)

6. Calculate  $R_{BIAS}$ : The minimum supply voltage for this circuit is 1.8 V. The REF1112 has a current requirement of 1.2  $\mu$ A (max). Providing the REF1112 with 2  $\mu$ A of supply current assures proper operation. Therefore,  $R_{BIAS}$  is as given by Equation 7.

$$R_{BIAS} = \frac{V_{BATTMIN}}{I_{BIAS}} = \frac{1.8 \text{ V}}{2 \text{ }\mu\text{A}} = 0.9 \text{ M}\Omega$$
 (7)

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# System Examples (continued)

#### 8.3.2 Window Comparator

Figure 18 shows the TLV2369 used as a window comparator. The threshold limits are set by V<sub>H</sub> and V<sub>L</sub>, with V<sub>H</sub> greater than  $V_L$ . When  $V_{IN}$  is less than  $V_H$ , the output of A1 is low. When  $V_{IN}$  is greater than  $V_L$ , the output of A2 is low. Therefore, both op amp outputs are at 0 V as long as V<sub>IN</sub> is between V<sub>H</sub> and V<sub>L</sub>. This architecture results in no current flowing through either diode, Q1 is in cutoff, with the base voltage at 0 V, and V<sub>OUT</sub> forced high.

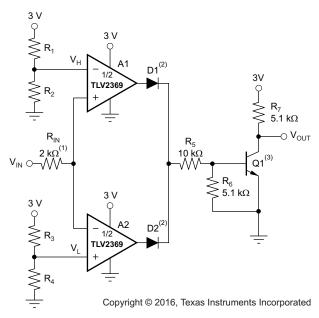


Figure 18. TLV2369 as a Window Comparator

If V<sub>IN</sub> falls below V<sub>L</sub>, the output of A2 is high, current flows through D2, and V<sub>OUT</sub> is low. Likewise, if V<sub>IN</sub> rises above V<sub>H</sub>, the output of A1 is high, current flows through D1, and V<sub>OUT</sub> is low. The window comparator threshold voltages are set as shown by Equation 8 and Equation 9:

$$V_{H} = \frac{R_{2}}{R_{1} + R_{2}}$$

$$V_{L} = \frac{R_{4}}{R_{3} + R_{4}}$$
(8)

# 9 Power Supply Recommendations

The TLV369 family is specified for operation from 1.8 V to 5.5 V (±0.9 V to ±2.75 V); many specifications apply from -40°C to +125°C. The Typical Characteristics section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

## **CAUTION**

Supply voltages larger than 7 V can permanently damage the device (see the Absolute Maximum Ratings table).

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or highimpedance power supplies. For more detailed information on bypass capacitor placement; see the Layout Guidelines section.

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# 10 Layout

# 10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the
  operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance
  power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most
  effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to
  ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI)
  noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of
  the ground current. For more detailed information, see Circuit Board Layout Techniques, SLOA089.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep R<sub>F</sub> and R<sub>G</sub> close to the inverting input in order to minimize parasitic capacitance, as shown in Figure 19.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

# 10.2 Layout Example

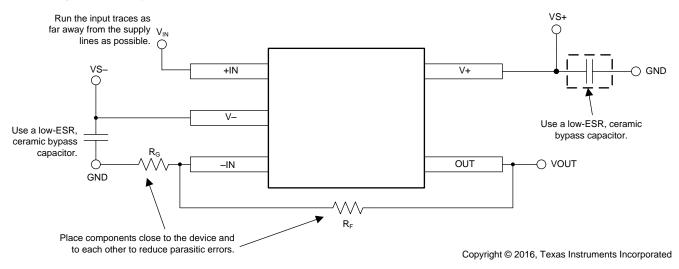
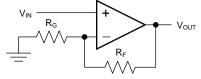


Figure 19. Operational Amplifier Board Layout for Noninverting Configuration



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Figure 20. Schematic Representation of Figure 19

Submit Documentation Feedback

SBOS757 - MAY 2016 www.ti.com

# 11 Device and Documentation Support

# 11.1 Documentation Support

#### 11.1.1 Related Documentation

The following documents are relevant to using the TLVx369, and are recommended for reference and available for download at www.ti.com, unless otherwise noted.

- REF1112 Data Sheet, SBOS283
- Circuit Board Layout Techniques, SLOA089
- Handbook of Operational Amplifier Applications, SBOA092
- Analog Engineer's Pocket Reference, SLWY038

#### 11.1.1.1 Related Links

Table 1 lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TLV369	Click here	Click here	Click here	Click here	Click here
TLV2369	Click here	Click here	Click here	Click here	Click here

# 11.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

# 11.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

# **Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

# 11.5 Glossary

SLYZ022 — TI Glossary.

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This glossary lists and explains terms, acronyms, and definitions.

# 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com

17-Jun-2025

## PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(6)
TLV2369IDGKR	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDGKR.A	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDGKT	Active	Production	VSSOP (DGK)   8	250   SMALL T&R	Yes	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDGKT.A	Active	Production	VSSOP (DGK)   8	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	13JV
TLV2369IDR	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV2369IDR.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV2369IDRG4	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV2369IDRG4.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369
TLV369IDCKR	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKR.A	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKR.B	Active	Production	SC70 (DCK)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKT	Active	Production	SC70 (DCK)   5	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKT.A	Active	Production	SC70 (DCK)   5	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K
TLV369IDCKT.B	Active	Production	SC70 (DCK)   5	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



# **PACKAGE OPTION ADDENDUM**

www.ti.com 17-Jun-2025

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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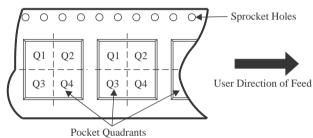
# TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2369IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2369IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2369IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV2369IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2369IDRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV369IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV369IDCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3



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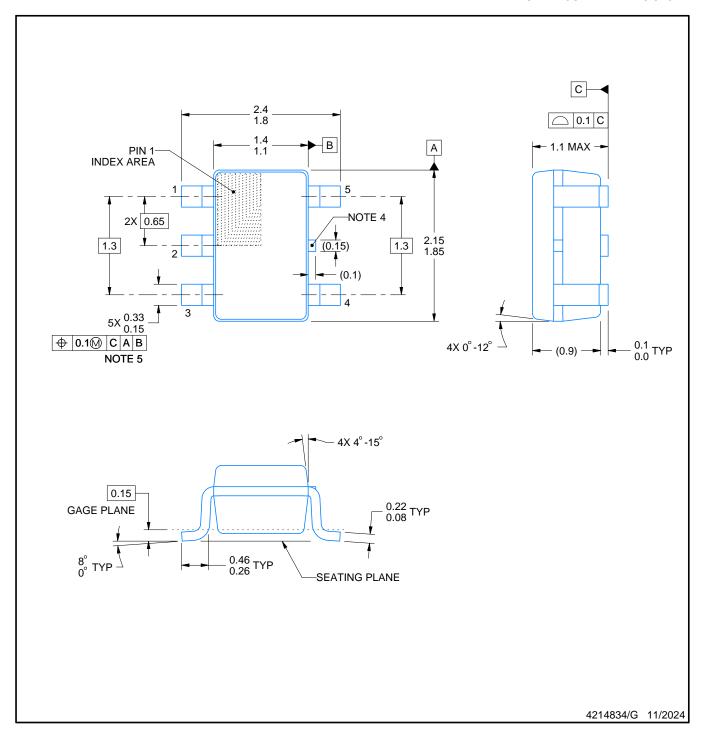


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2369IDGKR	VSSOP	DGK	8	2500	353.0	353.0	32.0
TLV2369IDGKT	VSSOP	DGK	8	250	353.0	353.0	32.0
TLV2369IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
TLV2369IDR	SOIC	D	8	2500	353.0	353.0	32.0
TLV2369IDRG4	SOIC	D	8	2500	353.0	353.0	32.0
TLV369IDCKR	SC70	DCK	5	3000	180.0	180.0	18.0
TLV369IDCKT	SC70	DCK	5	250	180.0	180.0	18.0



SMALL OUTLINE TRANSISTOR



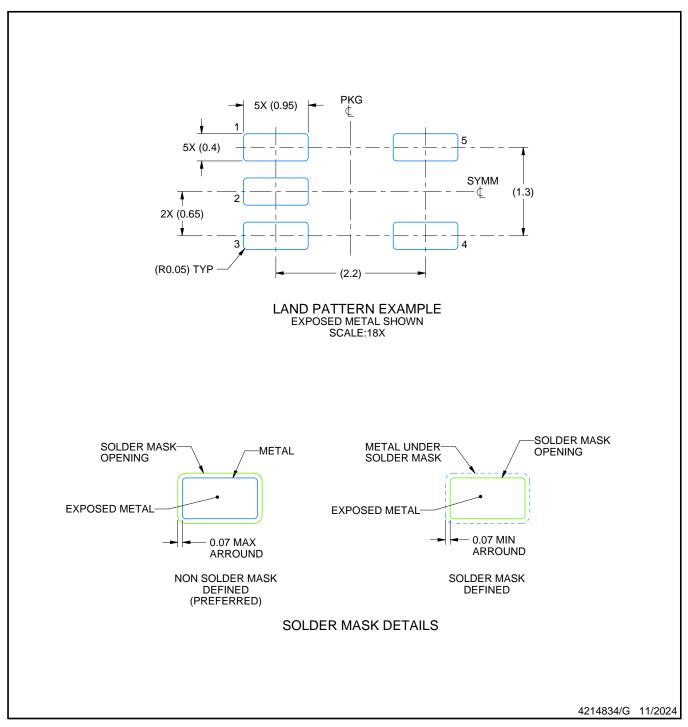
# NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
  3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



SMALL OUTLINE TRANSISTOR

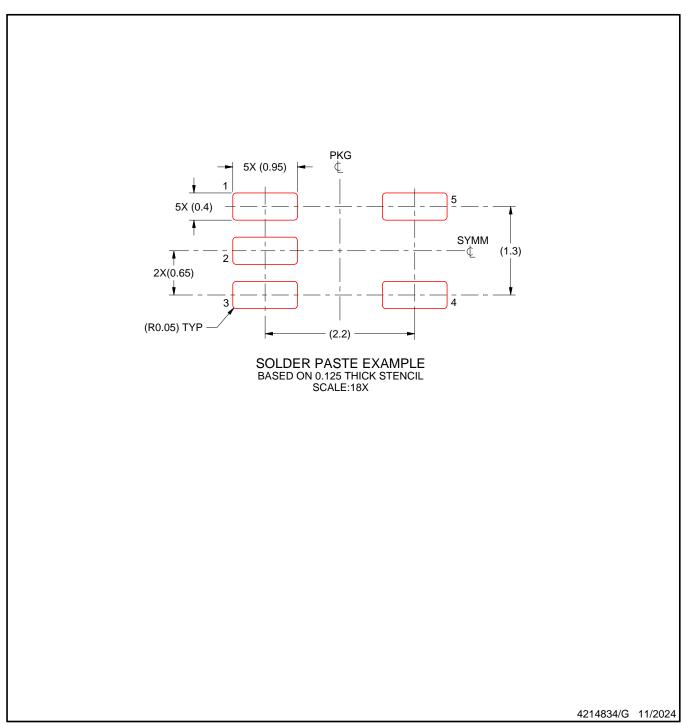


NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



# NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



# NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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